TECHNICAL DATA
DATA SHEET 4068, REV -

HERMETIC POWER MOSFET
N-CHANNEL

FEATURES:

- **55 Volt, 0.04 Ohm MOSFET**
- **Hermetically Sealed**
- **Add a "C" after the SHD for ceramic seals (SHDC220301)**
- **Surface Mount Package**

MAXIMUM RATINGS

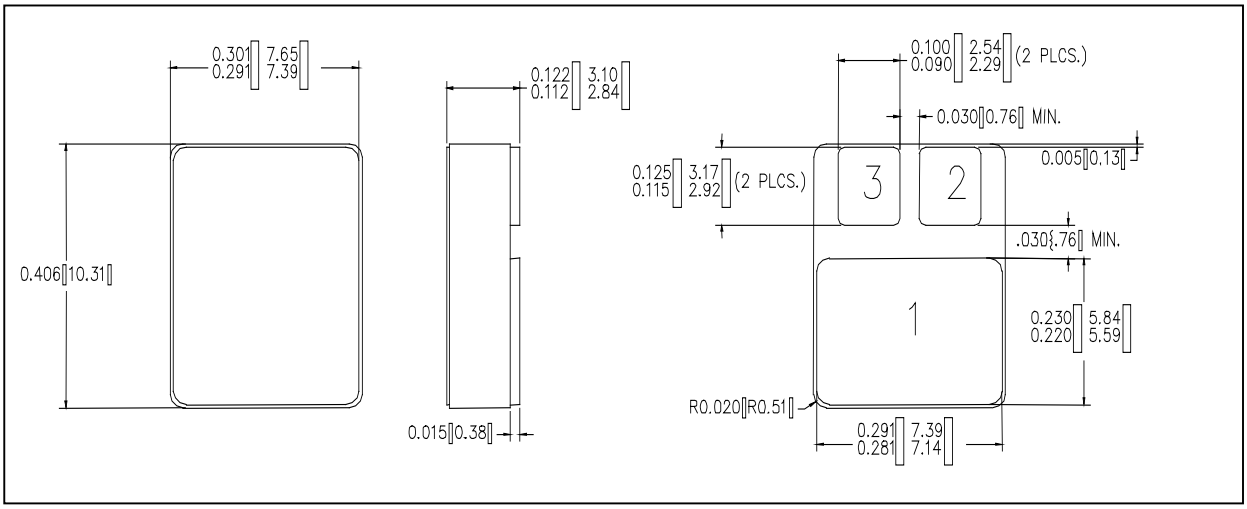
ALL RATINGS ARE AT T_A = 25°C UNLESS OTHERWISE SPECIFIED.

RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	V_{GS}	-	-	±20	Volts
CONTINUOUS DRAIN CURRENT V_{GS} = 10V, T_C = 25°C V_{GS} = 10V, T_C = 100°C	I_D	-	-	22 16	Amps
PULSED DRAIN CURRENT @ T_C = 25°C	I_{DM}	-	-	88	Amps
OPERATING AND STORAGE TEMPERATURE	T_{OP}/T_{STG}	-55	-	+175	°C
TERMAL RESISTANCE JUNCTION TO CASE	$R_{\theta JC}$	-	-	3.1	°C/W
TOTAL DEVICE DISSIPATION @ T_C = 25°C	P_D	-	-	40	Watts

ELECTRICAL CHARACTERISTICS

DRAIN TO SOURCE BREAKDOWN VOLTAGE V_{GS} = 0V, I_D = 250 µA	BV_{DSS}	55	-	-	Volts
DRAIN TO SOURCE ON STATE RESISTANCE V_{GS} = 10V, I_D = 16A	$R_{DS(ON)}$	-	-	0.04	Ω
GATE THRESHOLD VOLTAGE V_{DS} = V_{GS}, I_D = 250µA	$V_{GS(th)}$	2.0	-	4.0	Volts
FORWARD TRANSCONDUCTANCE V_{DS} = V_{GS}, I_D = 16A	g_{fs}	8	-	-	S(1/Ω)
ZERO GATE VOLTAGE DRAIN CURRENT, T_J = 25°C (V_{DS} = 55V, V_{GS} = 0V), T_J = 125°C	I_{DSS}	-	-	25 250	µA
GATE TO SOURCE LEAKAGE FORWARD V_{GS} = 20V GATE TO SOURCE LEAKAGE REVERSE V_{GS} = -20V	I_{GSS}	-	-	100 -100	nA
TOTAL GATE CHARGE V_{GS} = 10V, GATE TO SOURCE CHARGE V_{DS} = 44V, GATE TO DRAIN CHARGE I_D = 16A	Q_g Q_{gs} Q_{gd}	-	-	34 7 14	nC
TURN ON DELAY TIME V_{DD} = 28V, RISE TIME I_D = 22A, TURN OFF DELAY TIME R_G = 13Ω, FALL TIME V_{GS} = 10V	$t_{d(ON)}$ t_r $t_{d(OFF)}$ t_f	-	-	12 28 30 30	nsec
DIODE FORWARD VOLTAGE T_J = 25°C,I_S = 22A V_{GS} = 0V	V_{SD}	-	-	1.6	Volts
REVERSE RECOVERY TIME T_J = 25°C, I_S = 22A, di/dt ≤ 100A/µsec,	t_{rr}	-	57	86	nsec
REVERSE RECOVERY CHARGE V_{DD} ≤ 25V	Q_{rr}	-	130	200	µC
INPUT CAPACITANCE V_{GS} = 0V, V_{DS} = 25V, OUTPUT CAPACITANCE f = 1.0MHz REVERSE TRANSFER CAPACITANCE	C_{iss} C_{oss} C_{rss}	-	700 250 100	-	pF

MECHANICAL DIMENSIONS: in Inches / mm



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PINOUT TABLE

DEVICE TYPE	PIN 1	PIN 2	PIN 3
N Channel Mosfet	DRAIN	GATE	SOURCE

TECHNICAL DATA

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